

Data Sheet

Customer : _____

Product : Insulated Gate Bipolar Transistor (IGBT) _____

Type : H40G3U600SC _____

Issued Date: 06-Sep.-2023 _____

Edition : Ver. 1 _____

Record of change

Date	Ver.	Description	Page
06-Sep.-2023	1		

VENDOR :

☐ **HITANO ENTERPRISE CORP.**

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MAKER :

☐ **Changzhou Starsea Electronics Co., Ltd.**

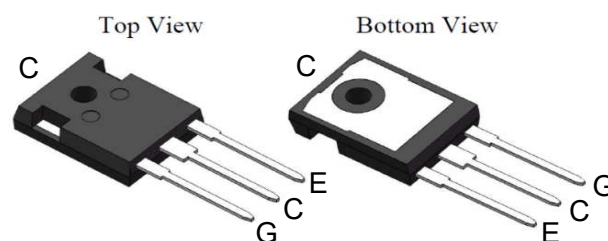
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FEATURES

- Low switching losses
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant



TO-247-3L

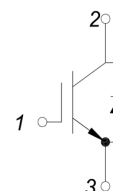
Case: TO-247-3L molded plastic body

Terminals : Leads solderable per MIL-STD-750, Method 2026

Polarity: As marked

Mounting Position: Any

1. Gate
2. Collector
3. Emitter



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J = 25^\circ\text{C}$	600	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C = 25^\circ\text{C}$	80	A
		$T_C = 100^\circ\text{C}$	40	
I_{Cpuls}	Pulsed collector current, tp limited by T_{Jmax}		120	
P_{tot}	Power Dissipation Per IGBT	$T_C = 25^\circ\text{C}$	280	W
		$T_C = 100^\circ\text{C}$	110	
V_{RRM}	Repetitive Reverse Voltage	$T_J = 25^\circ\text{C}$	600	V
I_F	Average Forward Current	$T_C = 25^\circ\text{C}$	80	A
		$T_C = 100^\circ\text{C}$	40	
T_{Jmax}	Max. Junction Temperature		150	$^\circ\text{C}$
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-55~150	

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R _{th} Characteristics						
IGBT thermal resistance, junction - case(IGBT)	R _{th(j-c)}		-	-	0.446	°C/W
Diode thermal resistance, junction - case(per diode)	R _{th(j-c)}		-	-	0.68	°C/W
Thermal resistance junction - ambient	R _{th(j-a)}		-	-	40	°C/W

IGBT

Electrical Characteristic (at TC = 25 °C, unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=1mA$	4.0	5.7	7.0	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=40A, V_{GE}=15V, T_J=25^{\circ}C$		1.70	2.30	
I_{CES}	Collector Leakage Current	$V_{CE}=600V, V_{GE}=0V, T_J=25^{\circ}C$			1.0	mA
I_{GES}	Gate Leakage Current	$V_{CE}=0V, V_{GE}=\pm 20V, T_J=25^{\circ}C$	-250		250	nA
Q_g	Total Gate Charge	$V_{CE}=400V, I_C=40A, V_{GE}=15V$		165		nC
Q_{ge}	Gate emitter charge			15		
Q_{gc}	Gate collector charge			96		
$t_{d(on)}$	Turn on Delay Time	$V_{CE}=400V, I_C=40A, R_G=10\Omega, V_{GE}=15V, \text{Inductive Load}$	$T_J=25^{\circ}C$	42		ns
t_r	Rise Time		$T_J=25^{\circ}C$	50		
$t_{d(off)}$	Turn off Delay Time		$T_J=25^{\circ}C$	218		
t_f	Fall Time		$T_J=25^{\circ}C$	57		
E_{on}	Turn on Energy	$V_{CE}=400V, I_C=40A, R_G=10\Omega, V_{GE}=15V, \text{Inductive Load}$	$T_J=25^{\circ}C$	1.67		mJ
E_{off}	Turn off Energy		$T_J=25^{\circ}C$	0.97		
E_{ts}	Total Energy		$T_J=25^{\circ}C$	2.64		
C_{ies}	Input Capacitance	$V_{CE}=30V, V_{GE}=0V, f=1MHz$		2758		nF
C_{oes}	output Capacitance			170		
C_{res}	Reverse Transfer Capacitance			88		

Anti-Parallel Diode

Electrical Characteristic (at TC = 25 °C, unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=40A, V_{GE}=0V, T_J=25^{\circ}C$		1.60	2.0	V
t_{rr}	Reverse Recovery Time	$I_F=40A, di_F/dt=200A/\mu s, T_C=25^{\circ}C$		48		ns
I_{RRM}	Max. Reverse Recovery Current			2.0		A
Q_{RR}	Reverse Recovery Charge			106		nC

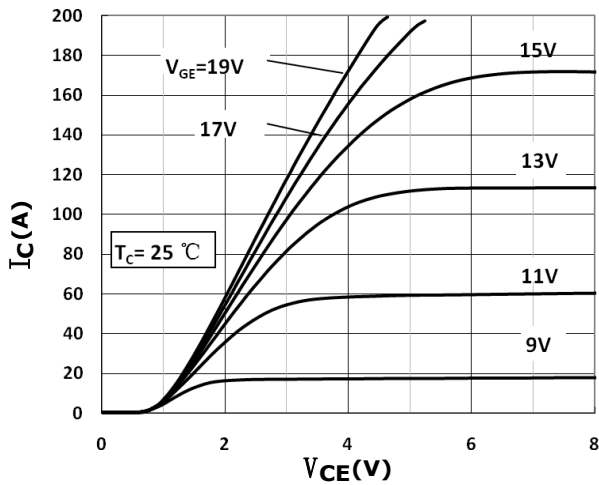


Figure 1. Output Characteristics

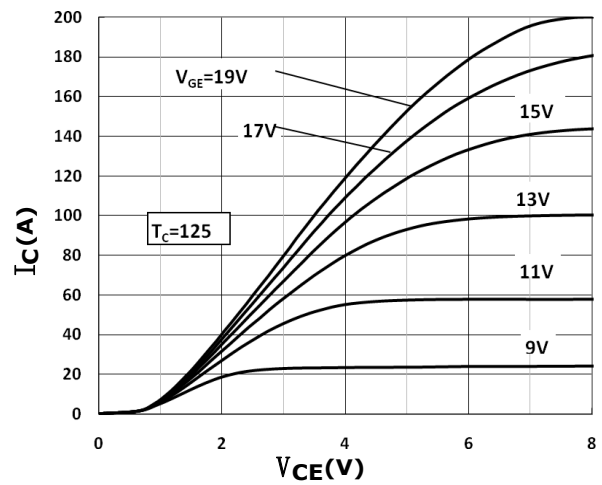


Figure 2. Output Characteristics

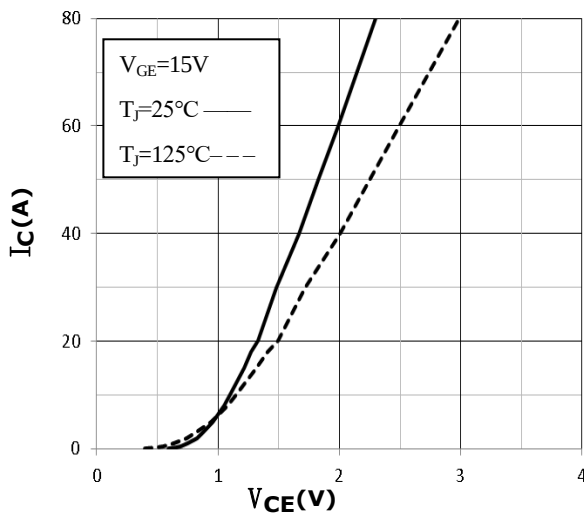


Figure 3. Saturation Voltage Characteristics

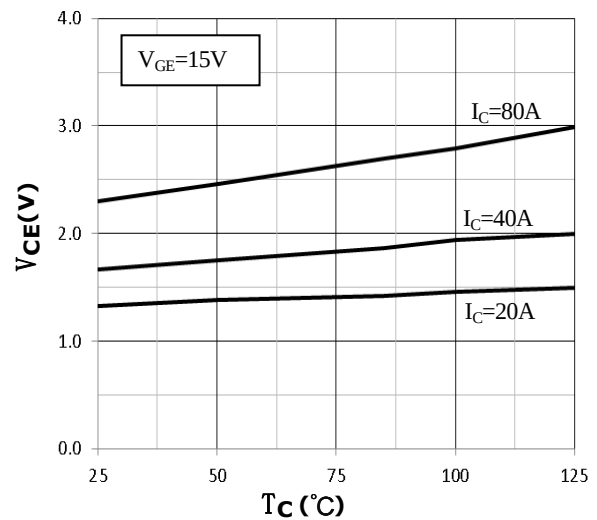


Figure 4. Saturation Voltage - TC Characteristics

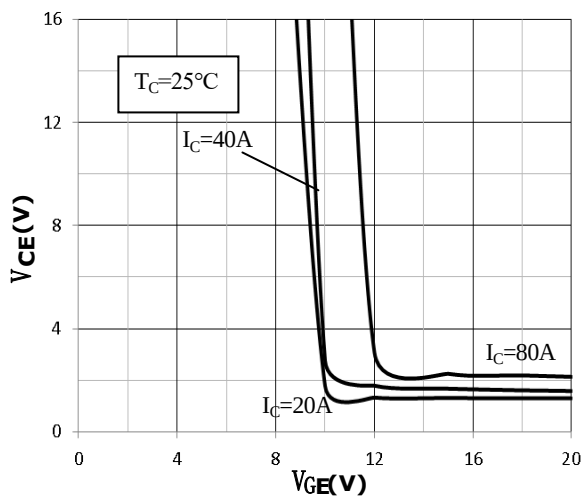


Figure 5. Saturation Voltage - V_{GE} Characteristics

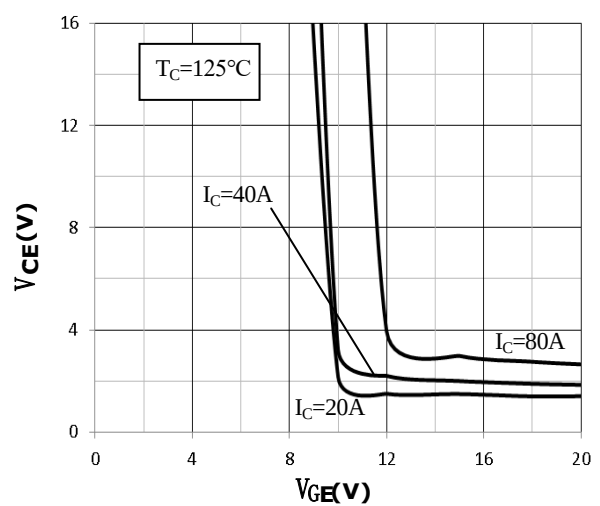


Figure 6. Saturation Voltage - V_{GE} Characteristics

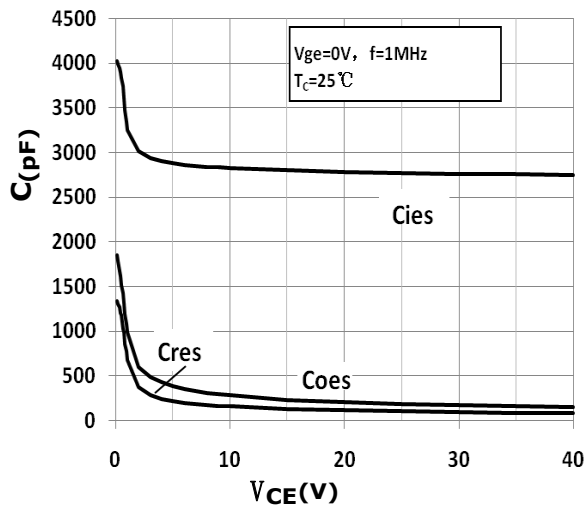


Figure 7. Capacitance Characteristics

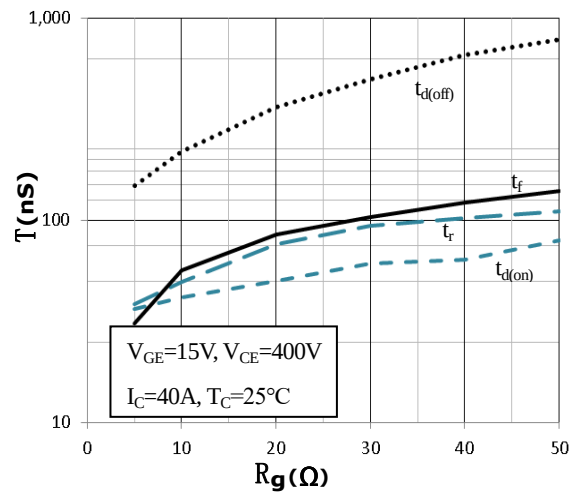


Figure 8. Switching Time- R_g Characteristics

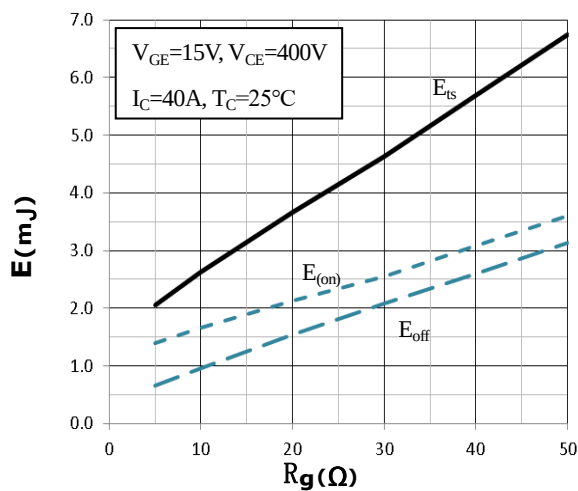


Figure 9. Switching loss- R_g Characteristics

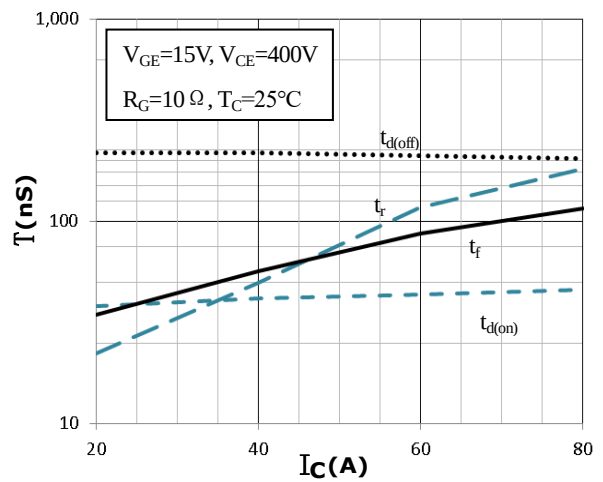


Figure 10. Switching Time- I_C Characteristics

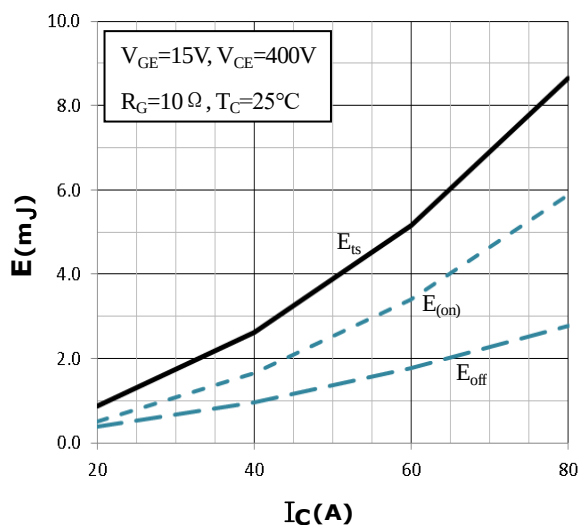


Figure 11. Switching loss - I_C Characteristics

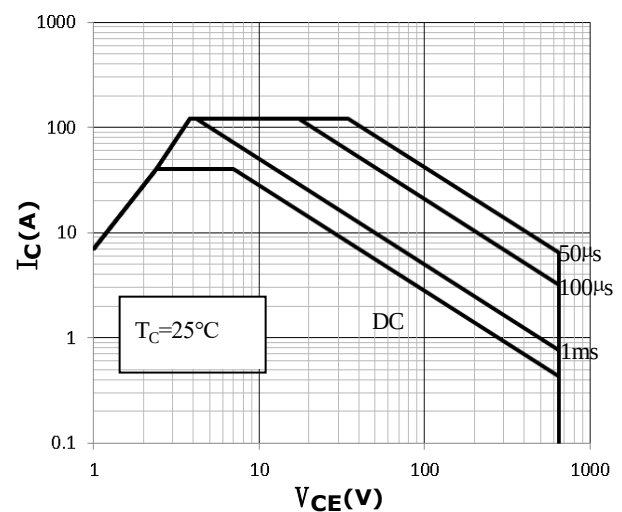


Figure 12. Forward Bias Safe Operating Area

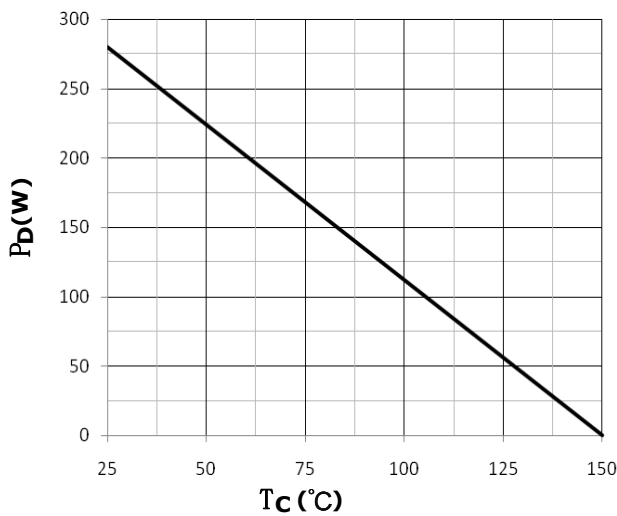


Figure 13. Power Dissipation- T_c Characteristics

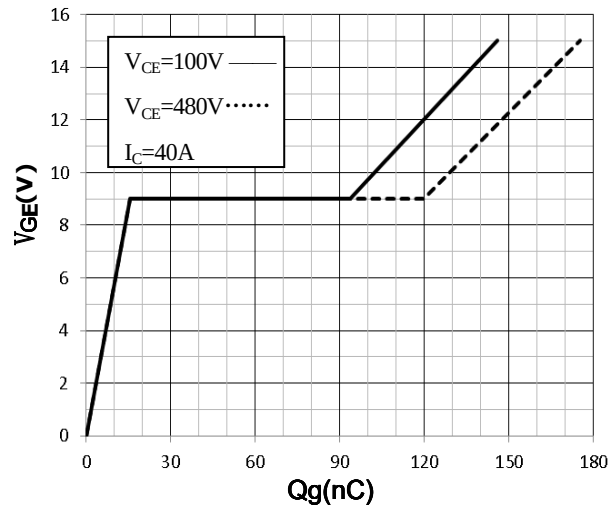


Figure 14. Gage Charge Characteristics

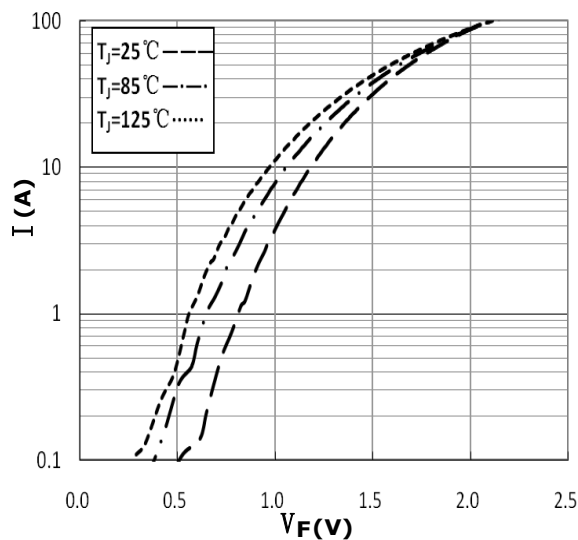


Figure 15. Diode Forward Characteristics

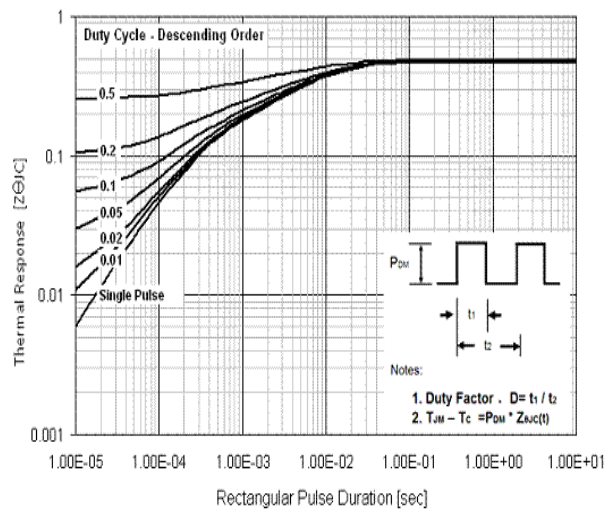


Figure 16. IGBT Transient Thermal Impedance

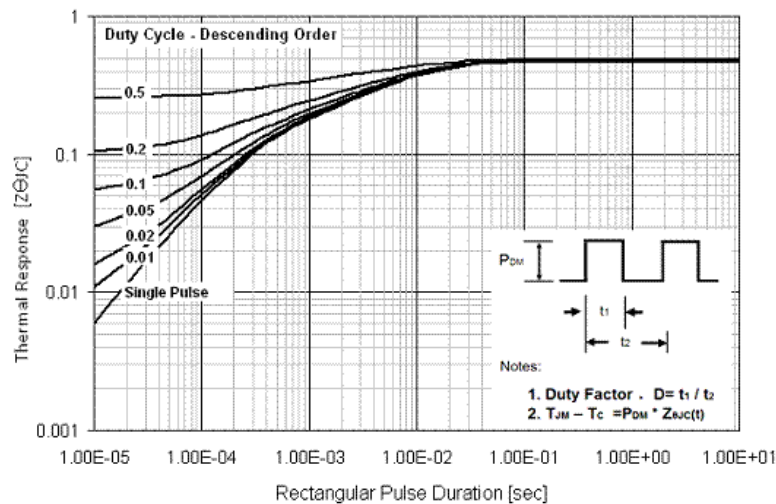
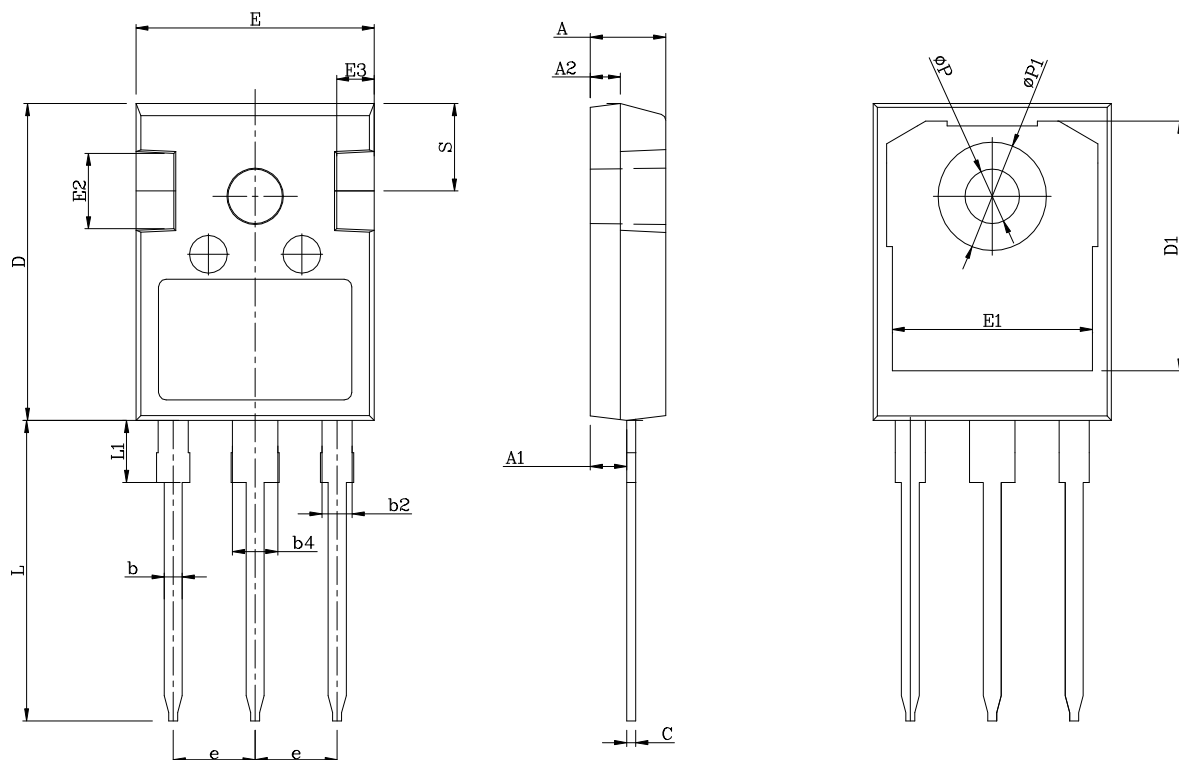


Figure 17. Transient Thermal Impedance

TO-247-3L



COMMON DIMENSIONS

SYMBOL	mm			SYMBOL	mm		
	Min	Nom	Max		Min	Nom	Max
A	4.80	5.00	5.20	E1	13.00	13.26	13.56
A1	2.23	2.41	2.59	E2	4.80	5.00	5.20
A2	1.85	2.00	2.15	E3	2.30	2.50	2.70
b	1.11	1.21	1.36	e	5.44BSC		
b2	1.91	2.01	2.21	L	19.82	19.92	20.22
b4	2.91	3.01	3.21	L1	3.94	4.12	4.30
c	0.51	0.61	0.75	ØP	3.40	3.60	3.80
D	20.80	21.00	21.30	ØP1	7.08	7.19	7.30
D1	16.25	16.55	16.85	S	6.15BSC		
E	15.50	15.80	16.10				